TLV760 100mA、30V、固定出力、リニア電圧レギュレータ

1 特長

- 広い入力電圧範囲: 最大30V
- 出力電流: 最大100mA
- 固定出力電圧3.3V、5V、12V、15Vバージョンで供給
- 動作時の接合部温度: −40℃～＋125℃
- 0.1µF以上のセラミック・コンデンサにより安定
- アクティブな熱保護と電流制限

2 アプリケーション

- スイッチングDC/DCコンバータのポスト・レギュレータ
- デジタルおよびアナログ回路のバイアス電源
- 家電製品
- パワー・ツール
- ファクトリ/ビルディング・オートメーション

3 概要

TLV760は、最大30Vの入力に対応する統合型のリニア電圧レギュレータです。TLV760は、動作温度範囲全体にわたり、100mAの全負荷時のドロップアウトが最大1.2Vとなっています。TLV760の標準のパッケージは、3ピンSOT-23パッケージです。

TLV760は3.3V、5V、12V、15Vで利用できます。TLV760シリーズはSOT-23パッケージを採用しているため、このデバイスはスペースの制約があるアプリケーションで使用できます。TLV760は、LM78Lxxシリーズおよび類似デバイスの小型版です。

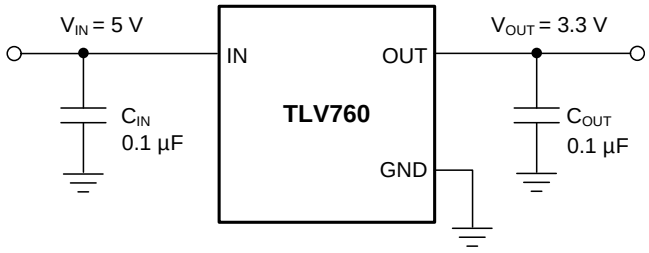
TLV760は、家電製品やオートメーション・アプリケーションなど、最大30Vの電圧過渡およびスパイクにさらされるアプリケーションでデジタルおよびアナログ回路をバイアスするように設計されています。このデバイスは、強力な内部過熱保護機能を備えており、グランド短絡や周囲温度の上昇、高い負荷、または高いドロップアウトといった事象により生じるおそれのあるダメージから保護することができます。

製品情報(1)

型番	パッケージ	本体サイズ(公称)
TLV760	SOT-23 (3)	2.92mm×1.30mm

(1) 提供されているすべてのパッケージについては、このデータシートの末尾にある注文情報を参照してください。

代表的なアプリケーション回路



目次

4 改訂履歴

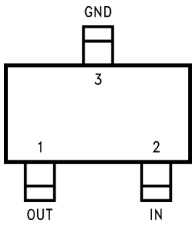
資料番号末尾の英字は改訂を表しています。その改訂履歴は英語版に準じています。

2017年6月発行のものから更新 **Page**

- Changed description of pin 1 to "OUT" and pin 2 to "IN" to correct error ... 3

5 Pin Configuration and Functions

DBZ Package
3-Pin SOT-23
Top View



Pin Functions

PIN		I/O	DESCRIPTION
NO.	NAME		
1	OUT	O	Output voltage, a ceramic capacitor greater than or equal to 0.1 μF is need for the stability of the device. (1)
2	IN	I	Input voltage supply — TI recommends a capacitor of value greater than 0.1 μF at the input. (1)
3	GND	—	Common ground

(1) See *External Capacitors* for more details.

6 Specifications

6.1 Absolute Maximum Ratings(1)

	MIN	MAX	UNIT
Input voltage (IN to GND)	–0.3	35	V
Output Voltage (OUT)		V_{IN} + 0.3	V
Output Current		Internally limited(2)	mA
Junction temperature	–40	150	°C
Storage temperature, T_{stg}	−65	150	°C

(1) Stresses beyond those listed under *Absolute Maximum Ratings*(1) may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
(2) See *Recommended Operating Conditions* section for more details.

6.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001(1)	±2000	V
		Charged-device model (CDM), per JEDEC specification JESD22-C101(2)	±500	

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

	MIN	MAX	UNIT
Maximum input voltage (IN to GND)		30	V
Output current (I_{OUT})		100	mA
Input and output capacitor (C_{OUT})	0.1		µF
Junction temperature, T_J	–40	125	°C

6.4 Thermal Information

THERMAL METRIC(1)		TLV760 DBZ (SOT-23) 3 PINS	UNIT
$R_{\theta JA}$	Junction-to-ambient thermal resistance	275.2	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	92.8	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	56.8	°C/W
ψ_{JT}	Junction-to-top characterization parameter	2.9	°C/W
ψ_{JB}	Junction-to-board characterization parameter	55.6	°C/W

(1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report.

6.5 Electrical Characteristics

Typical and other limits apply for $T_A = T_J = 25°C$, $V_{OUT(NOM)}$ = 3.3 V, 5 V, 12 V, and 15 V, unless otherwise specified.

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
V_{OUT}	Output voltage accuracy	$V_{IN} = V_{OUT(NOM)}$+ 1.5 V, 1 mA ≤ I_{OUT} ≤ 100 mA		–4%		4%	V
		$V_{IN} = V_{OUT(NOM)}$ + 1.5 V, 1 mA ≤ I_{OUT} ≤ 100 mA, −40°C ≤ T_J ≤ 125°C		–5%		5%	
$\Delta V_{(\Delta VIN)}$	Line regulation	$V_{OUT(NOM)}$ + 1.5 V ≤ V_{IN} ≤ 30 V, I_{OUT} = 1 mA , −40°C ≤ T_J ≤ 125°C	$V_{OUT(NOM)}$ = 3.3 V, 5 V		10	30	mV
			$V_{OUT(NOM)}$ = 12 V, 15 V		14	45	
$\Delta V_{(\Delta IOUT)}$	Load regulation	V_{IN} =$V_{OUT(NOM)}$ + 1.5 V , 10 mA ≤ I_{OUT} ≤ 100 mA, −40°C ≤ T_J ≤ 125°C	$V_{OUT(NOM)}$ = 3.3 V, 5 V		20	45	mV
			$V_{OUT(NOM)}$ = 12 V, 15 V		45	80	
I_{GND}	Ground pin current	$V_{OUT(NOM)}$ + 1.5 V ≤ V_{IN} ≤ 30 V, no load, −40°C ≤ T_J ≤ 125°C			2	5	mA
V_{DO}	Dropout voltage	I_{OUT} = 10 mA			0.7	0.9	V
		I_{OUT} = 10 mA , −40°C ≤ T_J ≤ 125°C				1	
		I_{OUT} = 100 mA			0.9	1.1	
		I_{OUT} = 100 mA, −40°C ≤ T_J ≤ 125°C				1.2	
T_{SD}	Thermal shutdown temperature				150		°C

6.6 Typical Characteristics

Unless indicated otherwise, $V_{IN} = V_{NOM} + 1.5$ V, $C_{IN} = 0.1$ µF, $C_{OUT} = 0.1$ µF, and $T_A = 25°C$.

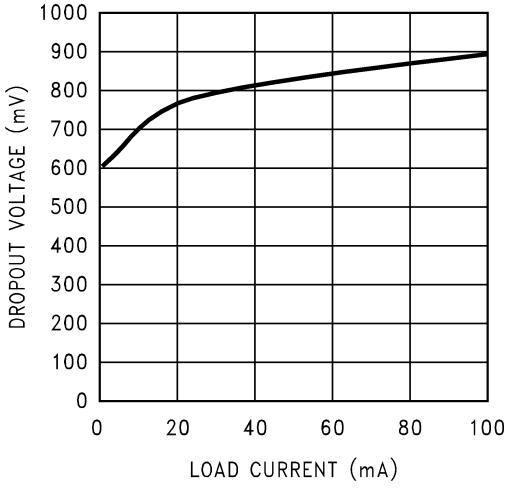


Figure 1. Dropout Voltage vs Load Current

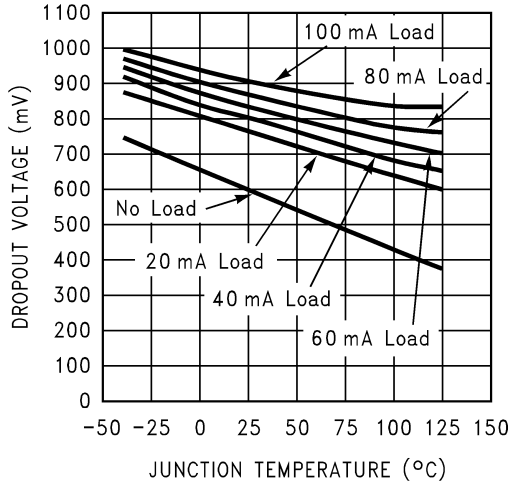


Figure 2. Dropout Voltage vs Junction Temperature

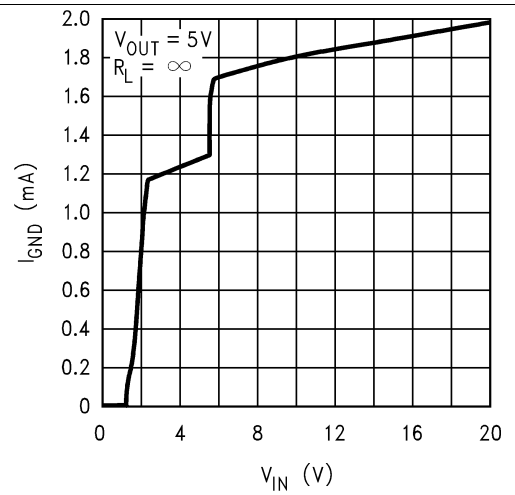


Figure 3. Ground Pin Current vs Input Voltage

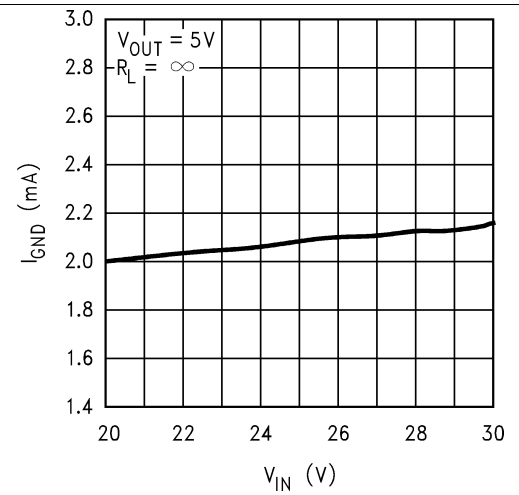


Figure 4. Ground Pin Current vs Input Voltage

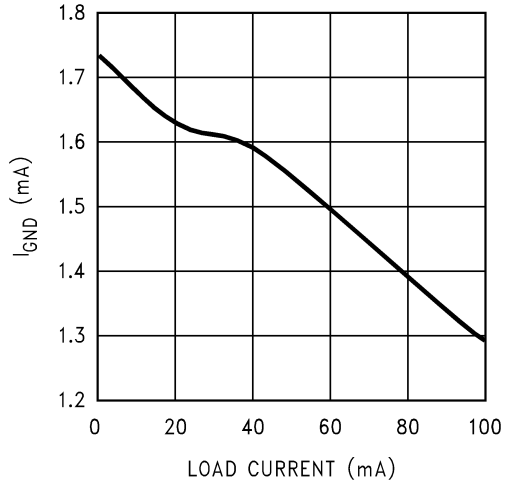


Figure 5. Ground Pin Current vs Load Current

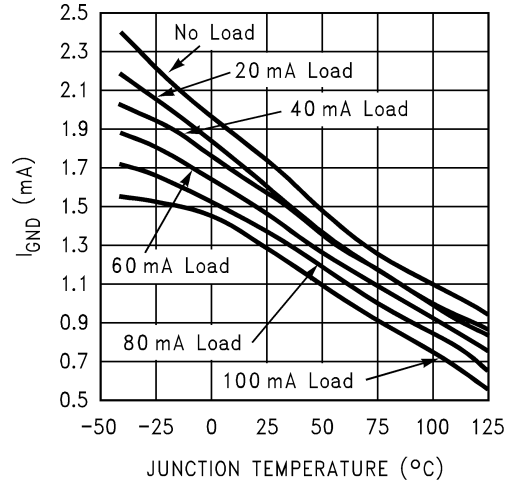


Figure 6. Ground Pin Current vs Junction Temperature

Typical Characteristics (continued)

Unless indicated otherwise, $V_{IN} = V_{NOM} + 1.5$ V, $C_{IN} = 0.1$ µF, $C_{OUT} = 0.1$ µF, and $T_A = 25°C$.

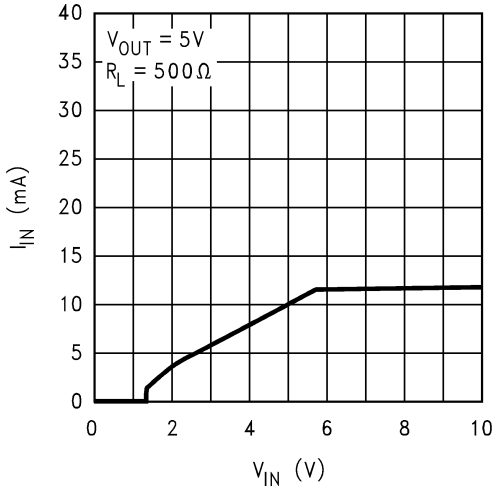


Figure 7. Input Current vs Input Voltage

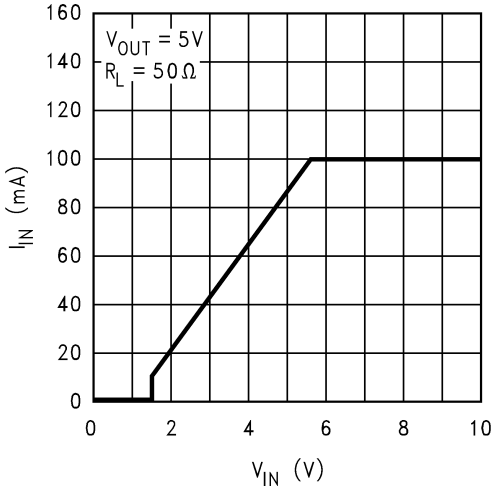


Figure 8. Input Current vs Input Voltage

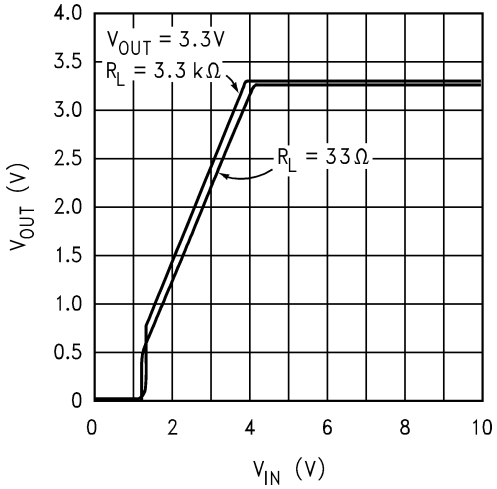


Figure 9. Output Voltage vs Input Voltage

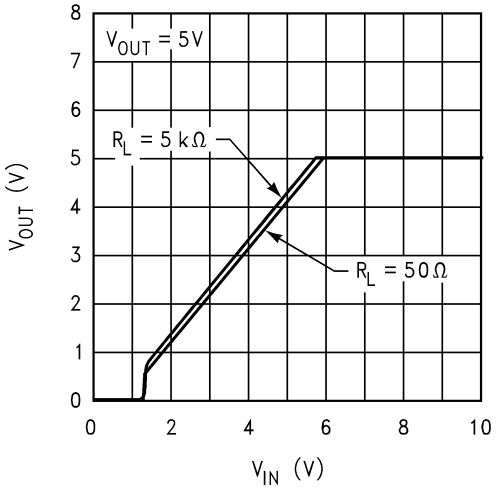


Figure 10. Output Voltage vs Input Voltage

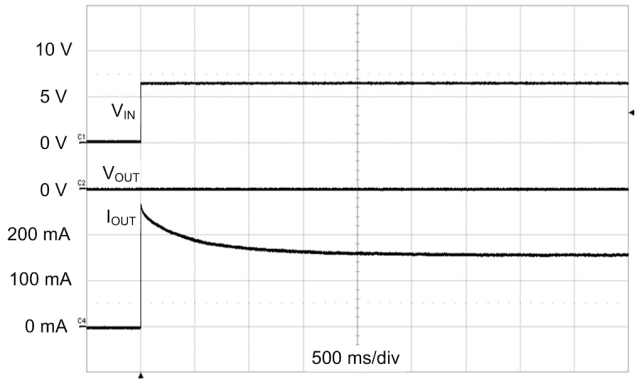


Figure 11. Output Short-Circuit Current

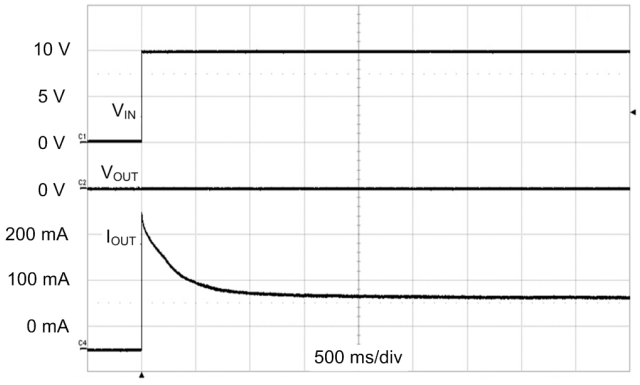


Figure 12. Output Short-Circuit Current

Typical Characteristics (continued)

Unless indicated otherwise, $V_{IN} = V_{NOM} + 1.5$ V, $C_{IN} = 0.1$ µF, $C_{OUT} = 0.1$ µF, and $T_A = 25°C$.

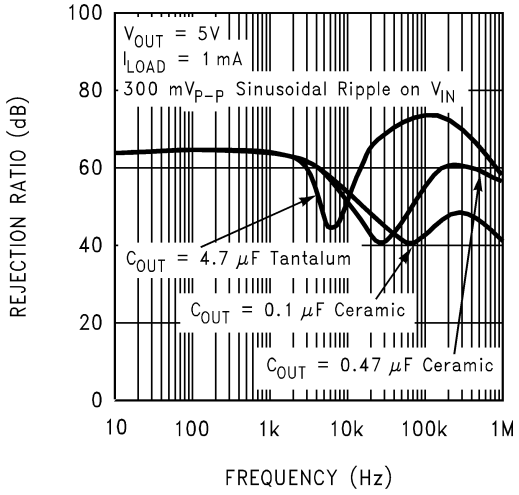


Figure 13. Power Supply Rejection Ratio

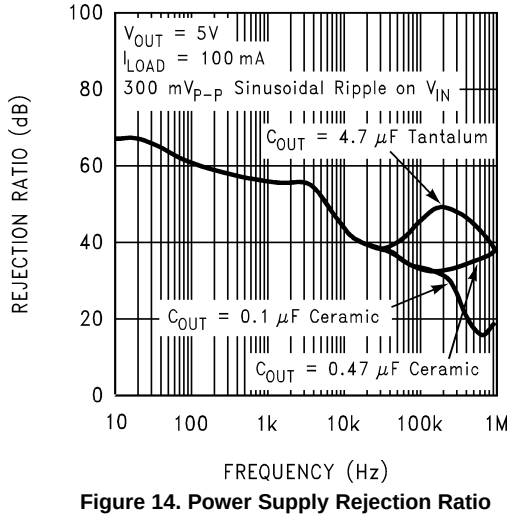


Figure 14. Power Supply Rejection Ratio

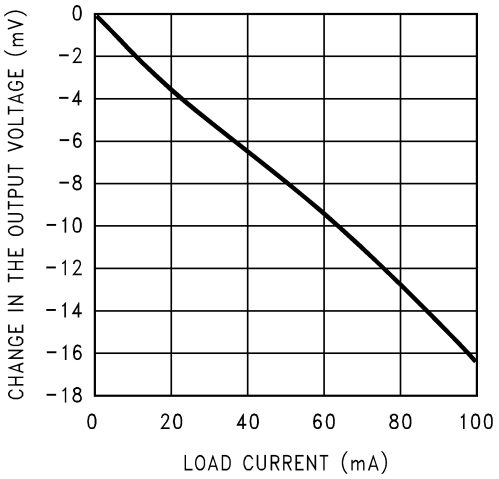


Figure 15. DC Load Regulation

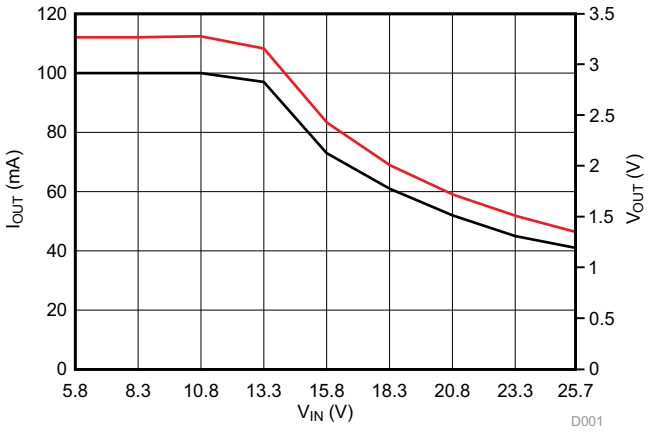


Figure 16. Output Current vs Input Voltage

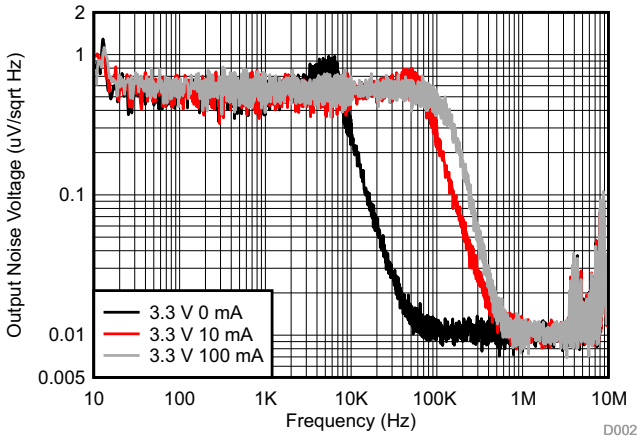


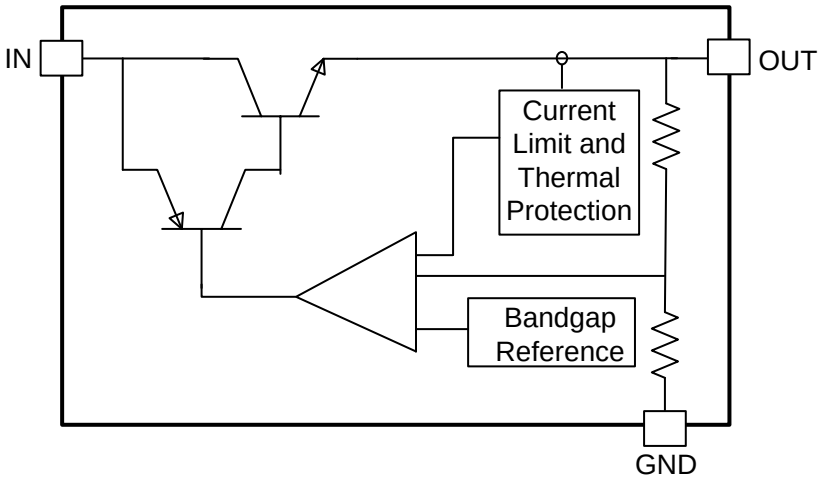
Figure 17. Output Spectral Noise Density vs Frequency

7 Detailed Description

7.1 Overview

The TLV760 is an integrated linear-voltage regulator with inputs that can be as high as 30 V. The TLV760 features quasi LDO architecture, which allows the usage of low ESR capacitors at the output. A ceramic capacitor with a capacitance value greater than or equal to 0.1 µF is adequate to keep the linear regulator in stable operation. The device has a rugged active junction thermal protection mechanism.

7.2 Functional Block Diagram



7.3 Feature Description

7.3.1 Thermal Protection

The TLV760 contains an active thermal protection mechanism, which limits the junction temperature to 150°C. This protection comes into action when the thermal junction temperature of the device tries to exceed 150°C. The output current of the device is limited or folded back to maintain the junction temperature.

The thermal protection follows Equation 1

$$P_D = (T_J - T_A) / R_{\theta JA} \quad (1)$$

where

- $P_D = (V_{IN} - V_{OUT})I_{OUT}$
- T_J is the junction temperature
- $R_{\theta JA}$ is the junction-to-ambient thermal resistance

When a high drop out condition occurs resulting in higher power dissipation across the device the output current is limited to maintain a constant junction temperature of 150°C. This rugged feature protects the device from higher power dissipation applications as well as the short to ground at the output.

This internal protection circuitry of TLV760 is intended to protect the devices against thermal overload conditions. The circuitry is not intended to replace proper heat sinking. Continuously running the TLV760 into thermal protection degrades device reliability.

For reliable operation, limit junction temperature to a maximum of 125°C. To estimate the thermal margin in a given layout, increase the ambient temperature until the thermal protection is triggered using worst case load and highest input voltage conditions.

Feature Description (continued)

7.3.2 Dropout Voltage

The TLV760 is a bipolar device with quasi LDO architecture. Being a bipolar device the dropout voltage of the device does not change significantly with output load current. The device has a maximum dropout across temperature of 1.2 V at 100-mA load current, which is a significant improvement over the traditional LM78Lxx devices.

7.4 Device Functional Modes

7.4.1 Normal Operation

The TLV760 operates with an input up to 30 V. Its tiny SOT-23 package and quasi-LDO architecture makes it suitable for providing a very tiny 100-mA bias supply. The device regulates to the nominal output voltage when all of the following conditions are met.

- The input voltage is greater than the nominal output voltage plus the dropout voltage ($V_{OUT(NOM)}$ + V_{DO}).
- The output current is less than or equal to 100 mA.
- The device junction temperature is less than the thermal protection temperature of 150°C.

8 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

8.1 Application Information

The TLV760 is a fixed output device which need only input and output capacitors to function. This section discusses the key aspects to implement this linear regulator in typical applications.

8.1.1 Fixed Output

TLV760 comes in fixed output voltage options, 3.3 V, 5 V, 12 V and 15 V. To ensure the proper regulated output, the input voltage should be greater than $V_{OUT(nom)} + V_{DO}$.

8.1.2 External Capacitors

8.1.2.1 Input and Output Capacitor Requirements

A minimum input and output capacitance value of 0.1 µF is required for stability and adequate transient performance. There is no specific equivalent series resistance (ESR) limitation, although excessively high ESR compromises transient performance. There is no specific limitation on a maximum capacitance value on the input or the output. However while selecting a capacitor, derating factors on the capacitance value should be considered. Use C0G, X7R, or X5R-type ceramic capacitors because these capacitors have minimal variation in capacitance value and ESR over temperature.

8.1.2.2 Load-Step Transient Response

The load-step transient response is the output voltage response by the linear regulator to a step change in load current. The depth of charge depletion immediately after the load step is directly proportional to the amount of output capacitance. However, larger output capacitances decrease any voltage dip or peak occurring during a load step, the control-loop bandwidth is also decreased, thereby slowing the response time. TI recommends to optimally scale output capacitors for a specific application and test for the output load transients.

8.1.3 Power Dissipation

Proper consideration should be given to device power dissipation, location of the circuit on the printed circuit board (PCB), and correct sizing of the thermal plane to ensure the device reliability. The PCB area around the regulator must be as free as possible of other heat-generating devices that cause added thermal stresses. To first-order approximation, power dissipation in the regulator depends on the input-to-output voltage difference and load conditions. Power dissipation can be calculated using The thermal protection follows Equation 1:

$$P_D = (T_J - T_A) / R_{\theta JA}$$

where

- $P_D = (V_{IN} - V_{OUT})I_{OUT}$
- T_J is the junction temperature
- $R_{\theta JA}$ is the junction-to-ambient thermal resistance (2)

Thus, at a given load current, input and output voltage, maximum power dissipation determines the maximum allowable ambient temperature (T_A) for the device, and vice versa. Power dissipation and junction temperature are most often related by the junction-to-ambient thermal resistance ($R_{\theta JA}$) of the combined PCB and device package and the temperature of the ambient air (T_A).

$R_{\theta JA}$ is highly dependent on the heat-spreading capability built into the particular PCB design, and therefore varies according to the total copper area, copper weight, and location of the planes. The $R_{\theta JA}$ recorded in *Thermal Information* is determined by the JEDEC standard, PCB, and copper-spreading area and is only used as a relative measure of package thermal performance.

Application Information (continued)

TLV760 integrates a rugged protection where the T_J is limited to 150°C. The maximum power dissipation depends on the ambient temperature and can be calculated using $P_D = (T_J – T_A) / R_{\theta JA}$, for example, substituting the absolute maximum junction temperature, 150°C for T_J, 50°C for T_A, and 275.2 °C/W for $R_{\theta JA}$, the maximum power that can be dissipated is 363 mW. More power can be safely dissipated at lower ambient temperatures. Less power can be safely dissipated at higher ambient temperatures. The power dissipation can be increased by 3.6 mW for each °C below 50°C ambient. It must be derated by 3.6 mW for each °C above 50°C ambient. Proper heat sinking enables the safe dissipation of more power.

8.2 Typical Application

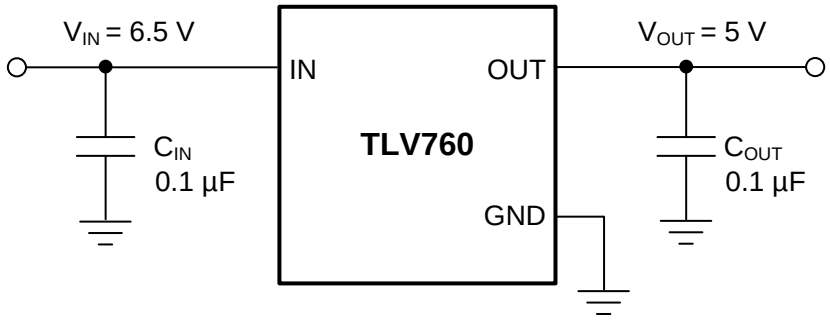


Figure 18. Typical Appication for the 5-V Option

8.2.1 Design Requirements

For typical TLV760 applications, use the parameters in Table 1.

Table 1. Design Parameters

DESIGN PARAMETER	EXAMPLE VALUE
Input voltage	6.5 V
Output voltage	5 V
Output current	100 mA

8.2.2 Detailed Design Procedure

The output for TLV76050 is internally set to 5 V. Input and output capacitors can be selected in accordance with the *External Capacitors*. Ceramic capacitances of 0.1 µF for both input and output are selected.

See the *Layout* section for an example of how to PCB layout the TLV760 to achieve best performance.

8.2.3 Application Curves

Unless indicated otherwise, V_{IN} = 6.5 V, V_{OUT} = 5 V, C_{OUT} = 0.1 µF, and T_A = 25°C.

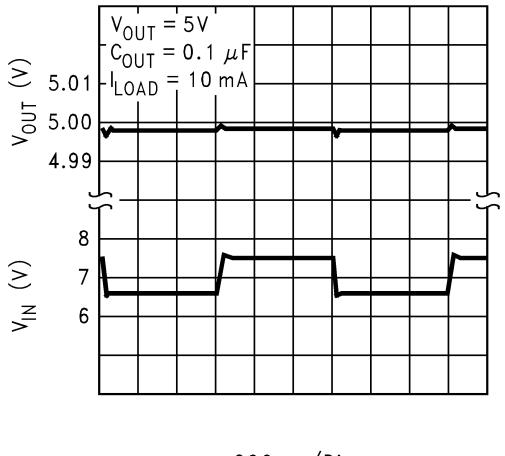


Figure 19. Line Transient Response

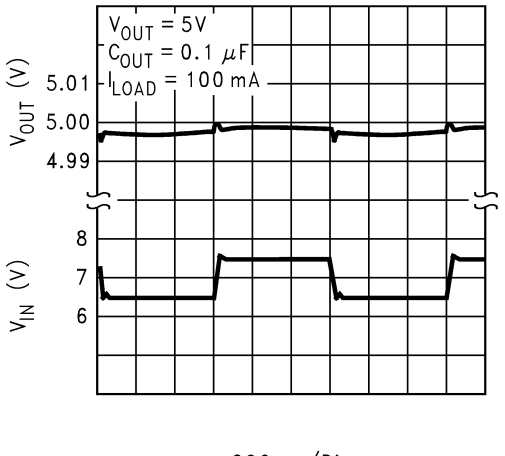


Figure 20. Line Transient Response

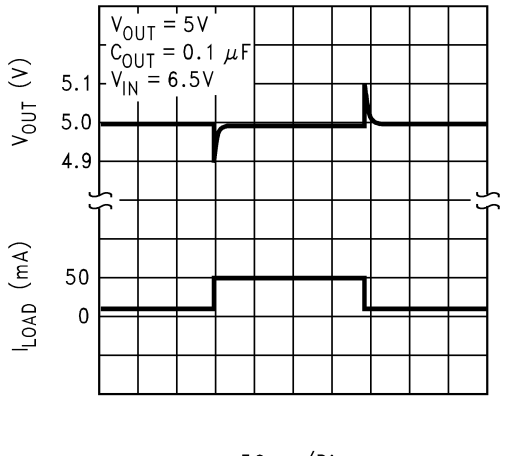


Figure 21. Load Transient Response

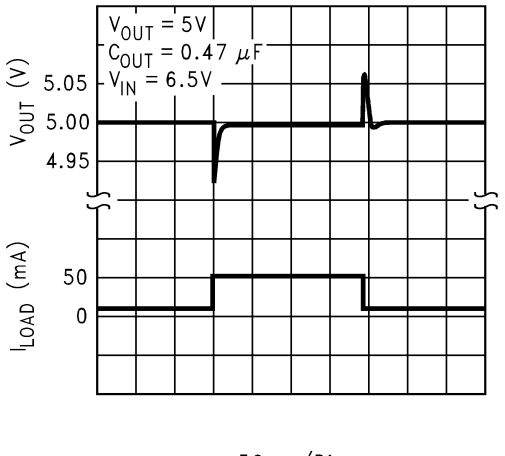


Figure 22. Load Transient Response

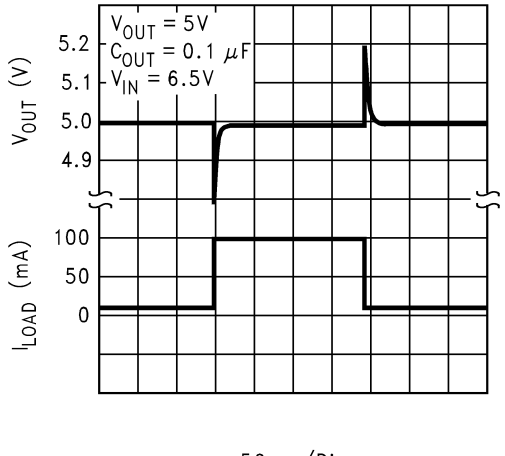


Figure 23. Load Transient Response

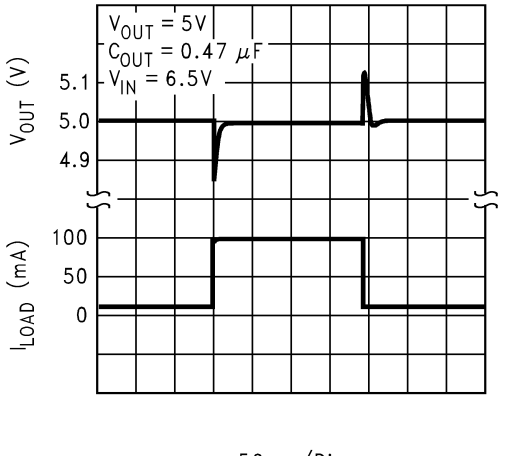


Figure 24. Load Transient Response

9 Power Supply Recommendations

The TLV760 is designed to operate from input voltage up to 30 V. If the input power supply has ripples, additional input and output capacitors with low ESR can help improve the PSRR at higher frequencies.

10 Layout

10.1 Layout Guidelines

General guidelines for linear regulator designs are to place all circuit components on the same side of the circuit board and as near as practical to the respective TLV760 pin connections. Place ground return connections to the input and output capacitors, and to the TLV760 ground pin as close as possible to each other, connected by a wide, component-side, copper surface. The use of vias and long traces to create TLV760 circuit connections is strongly discouraged and negatively affects system performance.

Use a ground reference plane, either embedded in the PCB itself or located on the bottom side of the PCB opposite the components. This reference plane serves to assure accuracy of the output voltage and to shield noise; it behaves similarly to a thermal plane to spread heat from the linear regulator. In most applications, this ground plane is necessary to meet thermal requirements.

10.2 Layout Example

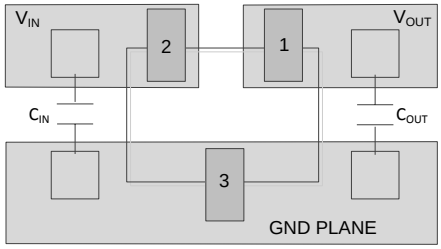


Figure 25. Layout Guideline for TLV760

11 デバイスおよびドキュメントのサポート

11.1 デバイス・サポート

11.1.1 関連資料

関連資料については、以下を参照してください。

『AN-1148 リニア・レギュレータ: 動作と補償の理論』

11.1.2 SPICEモデル

SPICEを使用した回路パフォーマンスのコンピュータによるシミュレーションは、アナログ回路やシステムのパフォーマンスを分析するため多くの場合に有用です。TLV760用のSPICEモデルは、TLV760製品フォルダの「シミュレーション・モデル」で入手できます。

11.1.3 デバイスの項目表記

表 2. 製品情報(1)

製品名	概要
TLV760**XXYYYZ**	**XX**は電圧指定子です。 **YYY**はパッケージ指定子です。 **Z**はパッケージ数量です。

(1) 最新のパッケージと発注情報については、このデータシートの末尾にあるパッケージ・オプションの付録を参照するか、www.ti.comにあるデバイスの製品フォルダをご覧ください。

11.2 ドキュメントの更新通知を受け取る方法

ドキュメントの更新についての通知を受け取るには、ti.comのデバイス製品フォルダを開いてください。右上の隅にある「*通知を受け取る*」をクリックして登録すると、変更されたすべての製品情報に関するダイジェストを毎週受け取れます。変更の詳細については、修正されたドキュメントに含まれている改訂履歴をご覧ください。

11.3 コミュニティ・リソース

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

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設計サポート ***TIの設計サポート*** **役に立つE2Eフォーラムや、設計サポート・ ツールをすばやく見つけることができます。技術サポート用の連絡先情報も参照できます。**

11.4 商標

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11.5 静電気放電に関する注意事項

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11.6 Glossary

SLYZ022 — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

12 メカニカル、パッケージ、および注文情報

以降のページには、メカニカル、パッケージ、および注文に関する情報が記載されています。この情報は、そのデバイスについて利用可能な最新のデータです。このデータは予告なく変更されることがあり、ドキュメントが改訂される場合もあります。本データシートのブラウザ版を使用されている場合は、画面左側の説明をご覧ください。

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
TLV76012DBZR	ACTIVE	SOT-23	DBZ	3	3000	RoHS & Green	SN	Level-1-260C-UNLIM	-40 to 125	18G	Samples
TLV76012DBZT	ACTIVE	SOT-23	DBZ	3	250	RoHS & Green	SN	Level-1-260C-UNLIM	-40 to 125	18G	Samples
TLV76015DBZR	ACTIVE	SOT-23	DBZ	3	3000	RoHS & Green	SN	Level-1-260C-UNLIM	-40 to 125	18C	Samples
TLV76015DBZT	ACTIVE	SOT-23	DBZ	3	250	RoHS & Green	SN	Level-1-260C-UNLIM	-40 to 125	18C	Samples
TLV76033DBZR	ACTIVE	SOT-23	DBZ	3	3000	RoHS & Green	SN	Level-1-260C-UNLIM	-40 to 125	18H	Samples
TLV76033DBZT	ACTIVE	SOT-23	DBZ	3	250	RoHS & Green	SN	Level-1-260C-UNLIM	-40 to 125	18H	Samples
TLV76050DBZR	ACTIVE	SOT-23	DBZ	3	3000	RoHS & Green	SN	Level-1-260C-UNLIM	-40 to 125	18I	Samples
TLV76050DBZT	ACTIVE	SOT-23	DBZ	3	250	RoHS & Green	SN	Level-1-260C-UNLIM	-40 to 125	18I	Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".
RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.
Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

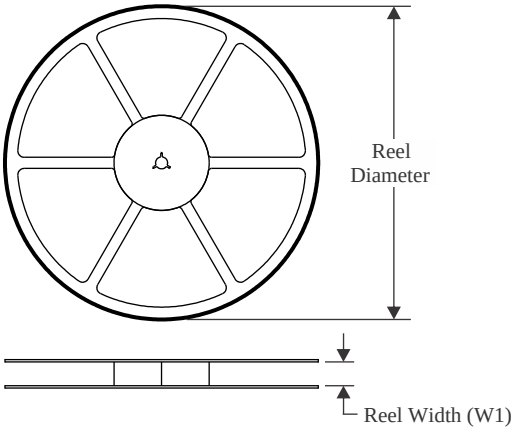
(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

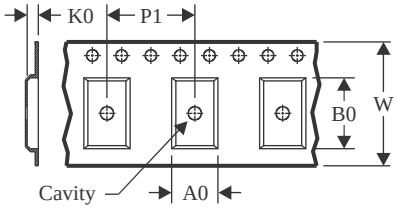
(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

TAPE AND REEL INFORMATION

REEL DIMENSIONS

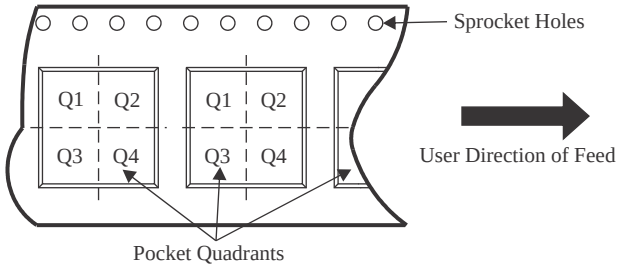


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

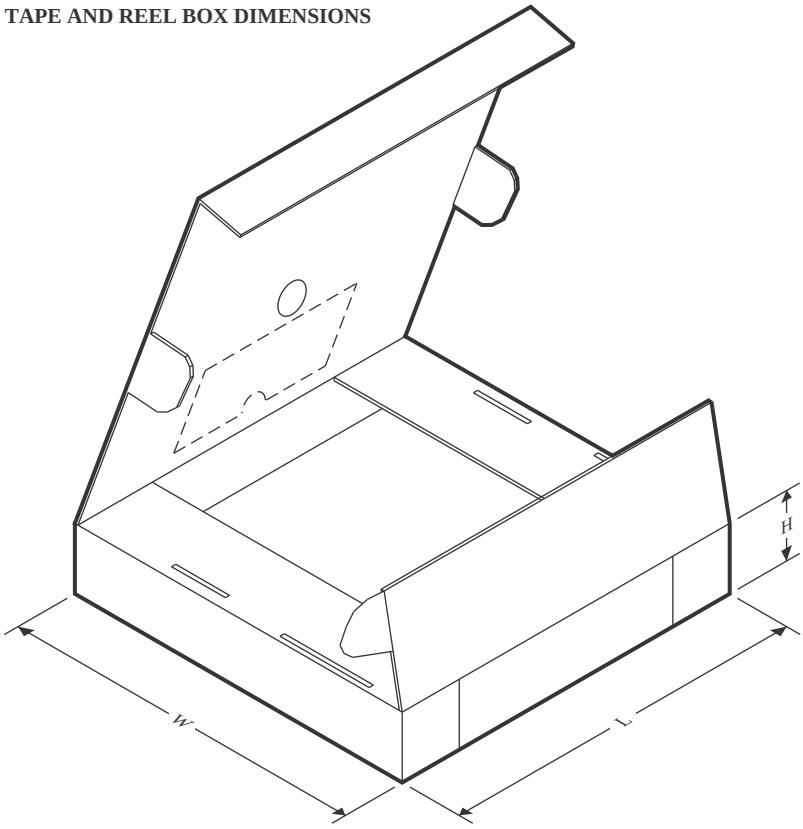
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TLV76012DBZR	SOT-23	DBZ	3	3000	178.0	8.4	3.3	2.9	1.22	4.0	8.0	Q3
TLV76012DBZT	SOT-23	DBZ	3	250	178.0	8.4	3.3	2.9	1.22	4.0	8.0	Q3
TLV76015DBZR	SOT-23	DBZ	3	3000	178.0	8.4	3.3	2.9	1.22	4.0	8.0	Q3
TLV76015DBZT	SOT-23	DBZ	3	250	178.0	8.4	3.3	2.9	1.22	4.0	8.0	Q3
TLV76033DBZR	SOT-23	DBZ	3	3000	178.0	8.4	3.3	2.9	1.22	4.0	8.0	Q3
TLV76033DBZT	SOT-23	DBZ	3	250	178.0	8.4	3.3	2.9	1.22	4.0	8.0	Q3
TLV76050DBZR	SOT-23	DBZ	3	3000	178.0	8.4	3.3	2.9	1.22	4.0	8.0	Q3
TLV76050DBZT	SOT-23	DBZ	3	250	178.0	8.4	3.3	2.9	1.22	4.0	8.0	Q3

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

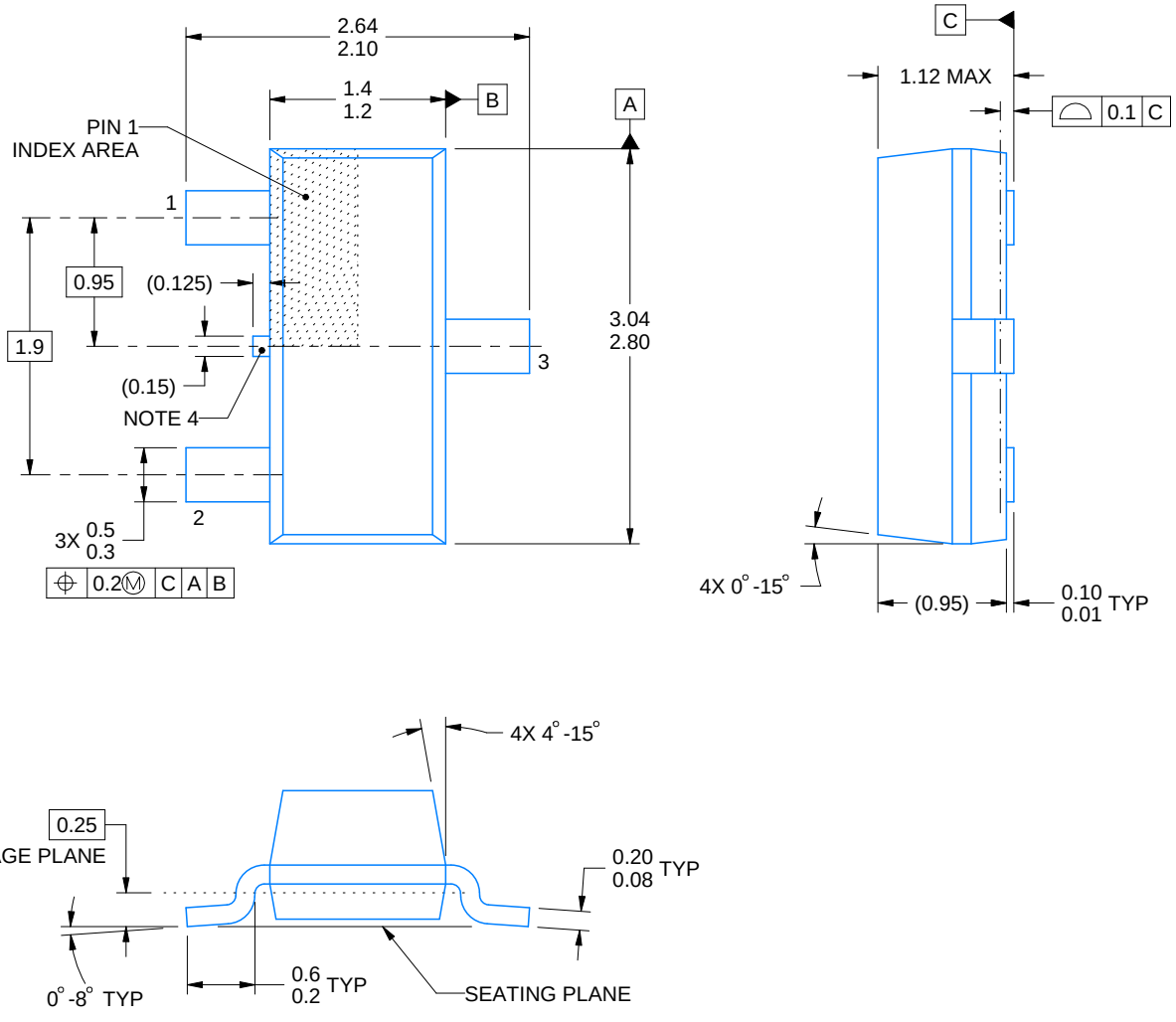
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TLV76012DBZR	SOT-23	DBZ	3	3000	208.0	191.0	35.0
TLV76012DBZT	SOT-23	DBZ	3	250	208.0	191.0	35.0
TLV76015DBZR	SOT-23	DBZ	3	3000	208.0	191.0	35.0
TLV76015DBZT	SOT-23	DBZ	3	250	208.0	191.0	35.0
TLV76033DBZR	SOT-23	DBZ	3	3000	208.0	191.0	35.0
TLV76033DBZT	SOT-23	DBZ	3	250	208.0	191.0	35.0
TLV76050DBZR	SOT-23	DBZ	3	3000	208.0	191.0	35.0
TLV76050DBZT	SOT-23	DBZ	3	250	208.0	191.0	35.0

PACKAGE OUTLINE

DBZ0003A

SOT-23 - 1.12 mm max height

SMALL OUTLINE TRANSISTOR



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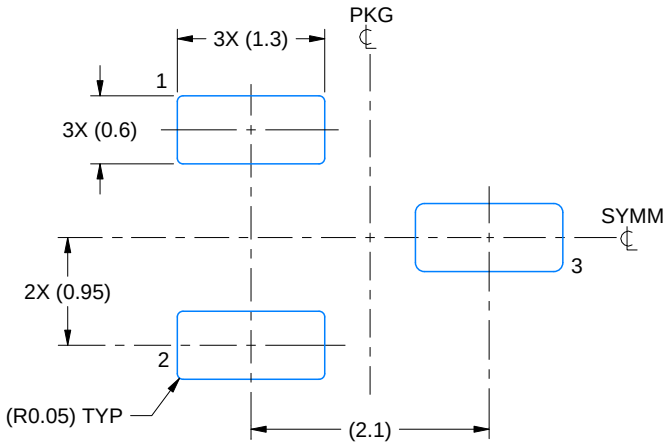
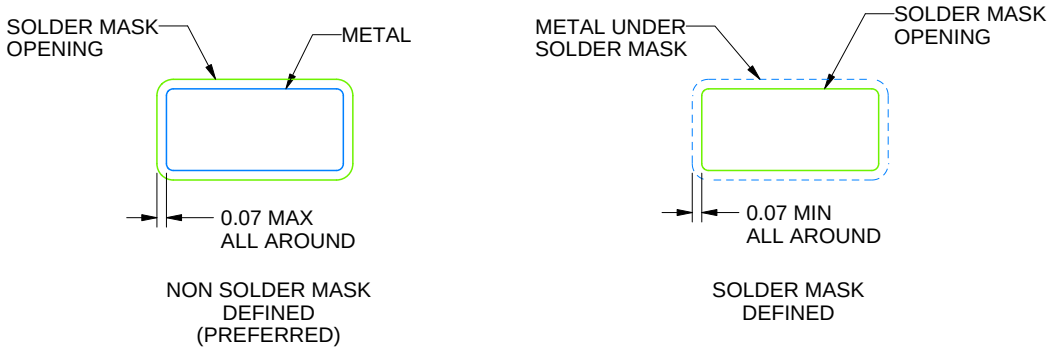
NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. Reference JEDEC registration TO-236, except minimum foot length.
4. Support pin may differ or may not be present.
5. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.25mm per side



LAND PATTERN EXAMPLE
SCALE:15X



SOLDER MASK DETAILS

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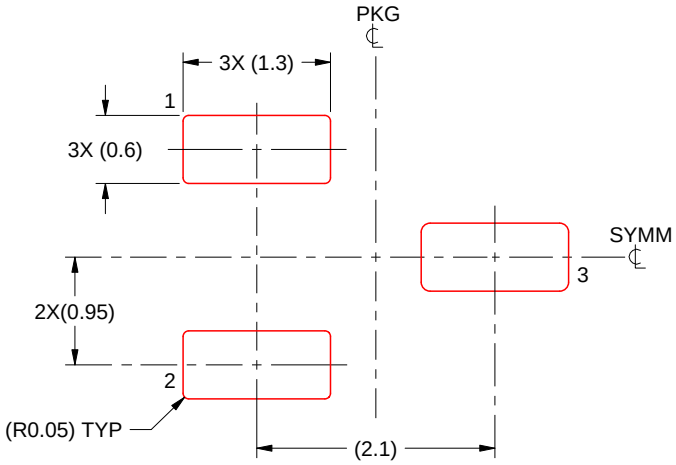
NOTES: (continued)

5. Publication IPC-7351 may have alternate designs.
6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SOLDER PASTE EXAMPLE
BASED ON 0.125 THICK STENCIL
SCALE:15X

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NOTES: (continued)

7. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
8. Board assembly site may have different recommendations for stencil design.

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